Electronic Supplementary Material (ESI) for

Poly(imide-benzoxazole) gate insulators with high thermal resistance for so lution-processed flexible indium-zinc oxide thin-film transistors

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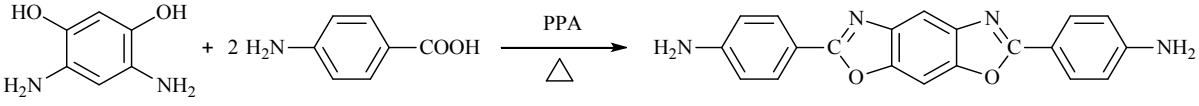
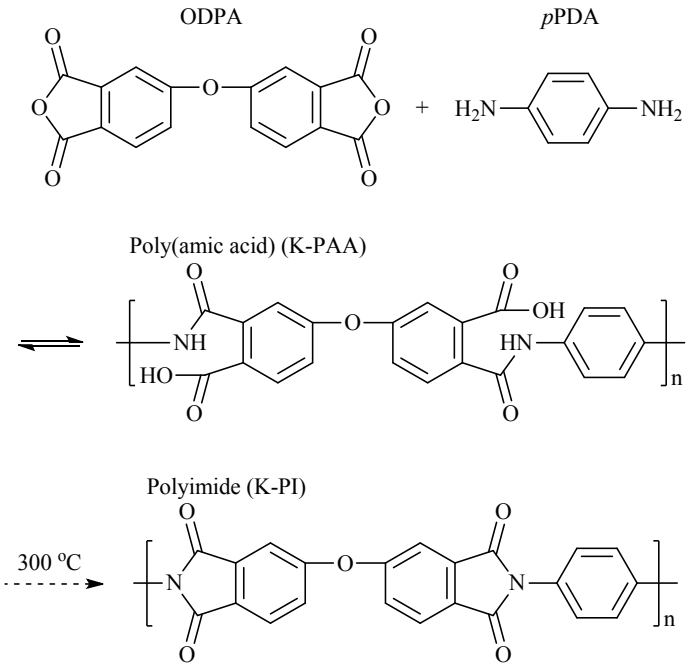


Scheme S1 Synthetic route to BODA.



Scheme S2 Synthetic route to K-PI gate insulator.

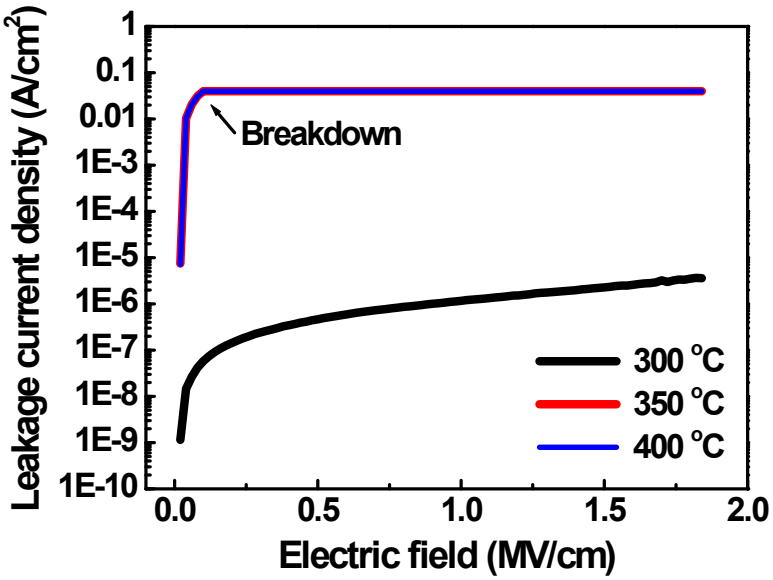


Fig. S1 Electric field-dependent leakage current densities of 500 nm-thick K-PI films after po st-annealing at 300 ˚C, 350 ˚C and 400 ˚C.

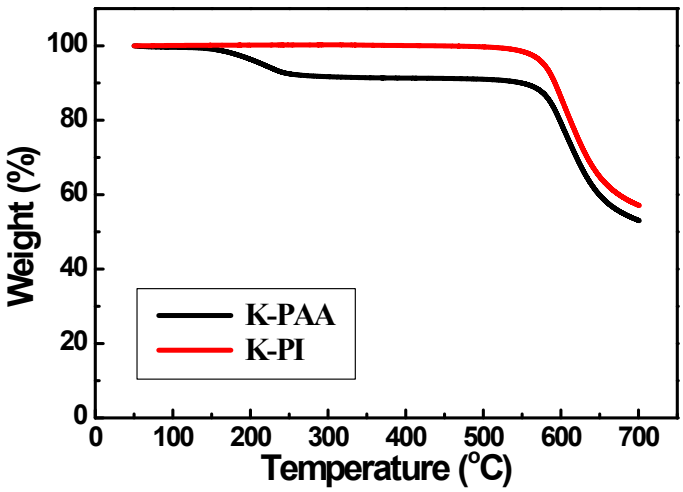


Fig. S2 TGA results of K-PAA and K-PI.

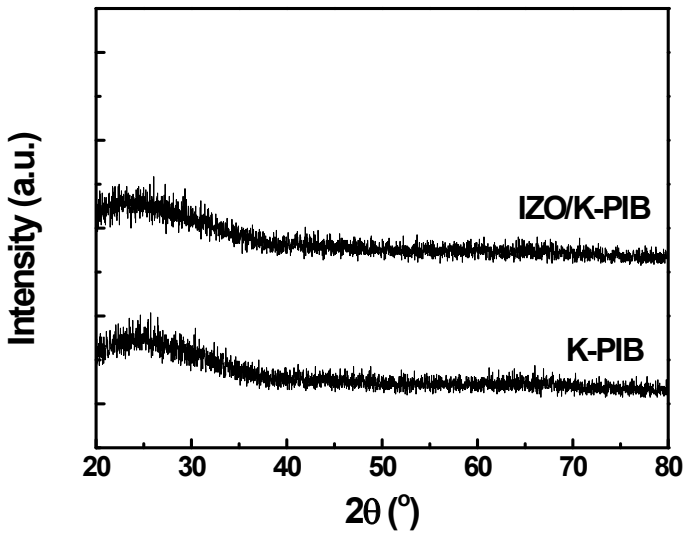


Fig. S3 XRD patterns of K-PIB and IZO/K-PIB films.

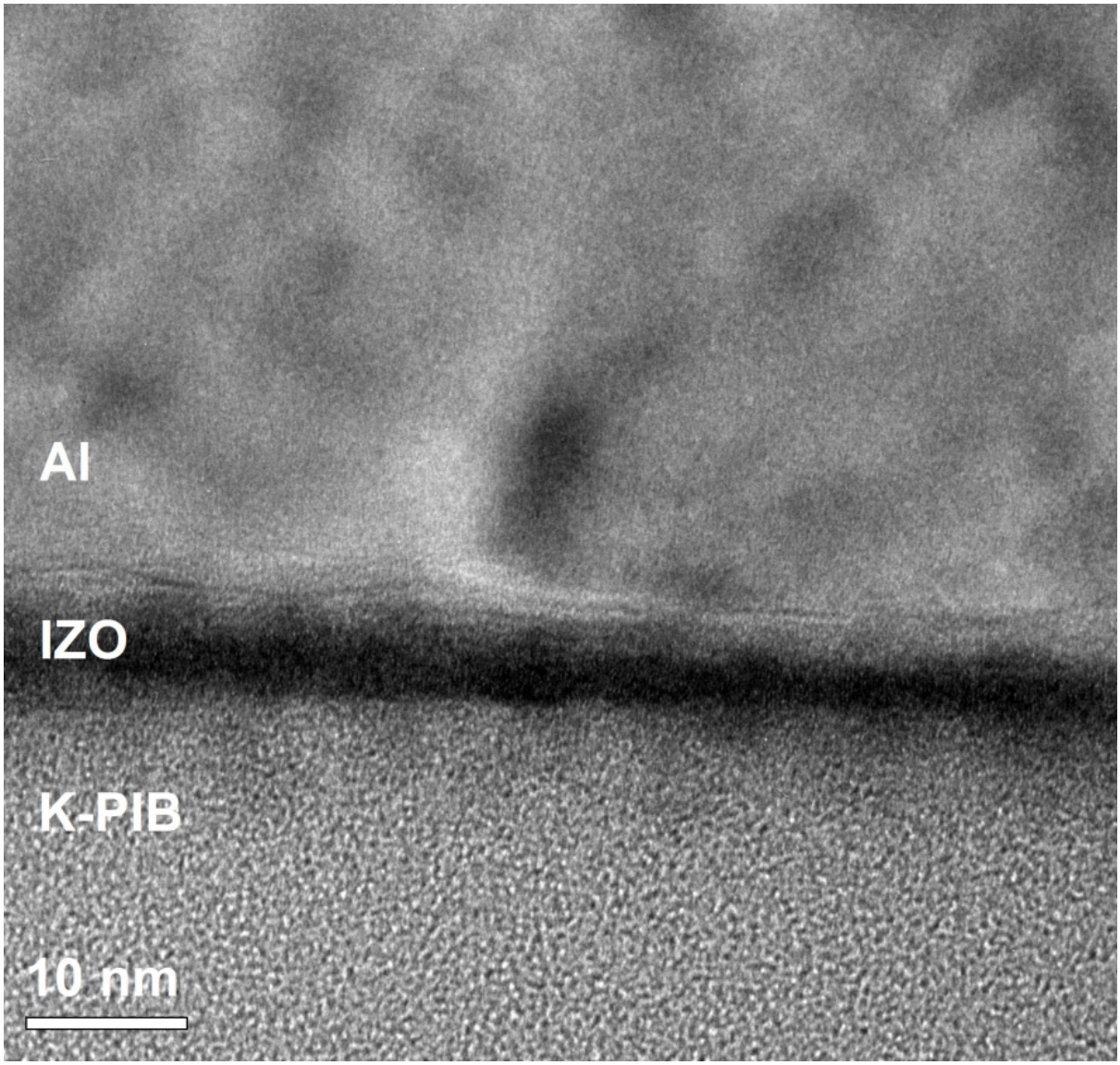


Fig. S4 Cross-sectioned TEM image of IZO layer on K-PIB film.